Application No.: 09/632,425 Attorney Docket No.: 16301-028300US JAN 0 3 2001 FORM PTO-1449 (Modified) LIST OF PATENTS AND PUBLICATIONS FOR Applicant: Fabrice Geiger et al. RECEIVED Unassigned APPLICANT'S INFORMATION VISCLOSURE Filing Date: August 4, 2000 STATEMENT (Use several sheets if recessary) JAN 1 0 2001 U.S. PATENT DOCUMENTS Page 1 Reference Designation Filing Date Date Name Document No. Examiner Initial (If Appropriate) 3/4/96 438 790 9/8/98 Cho 5,804,509 AA759 6/7/95 257 8/4/98 Gnade et al. 5,789,819 AΒ 6/7/95 238-437 Fukada AC 5,753,564 5/19/98 4/12/96 257 522 Havemann et al. 9/16/97 AD 5,668,398 4/24/96 579 427 Lee et al. ΑE 5,660,895 8/26/97 8/31/94 427 539 8/12/97 Park et al. 5,656,337 ΑF 574 2/10/95 427 11/5/96 Qian et al. 5,571,576 AG 6/7/95 638 Gnade et al. 257 5,561,318 10/1/96 ΑH 235 1/9/95 437-Maeda et al. 9/10/96 5,554,570 ΑI 6/23/950 195 Jang et al. 437 7/16/96 ΑJ 5,536,681 607/94 437~ 238 \bigcirc Ohta 5,525,551 6/11/96 ΑK 6/23/94 437-247 Cho et al. 4/2/96 5,504,042 AL231 6/7/94 437 Gnade et al. 5,494,858 2/27/96 AM 5/20/94 195 72 437 Havemann et al. 1/30/96 5,488,015 AN 192 10/29/93 437 Yamamoto et al. 1/23/96 AO 5,486,492 4/4/95 437 -238 Maeda et al. 1/16/96 AP 5,484,749 195 8/5/94 437 Havemann et al. 12/5/95 L AQ 5,472,913 5/20/94 437 238 Gnade et al. 11/28/95 AR 5,470,802 5/27/94 437 187 L 5,461,003 10/24/95 Havemann et al. AS 7/8/93 238-437 6/20/95 Moghadam AT 5,426,076 7/20/93 579 427 Hieber et al. AU 5,399,389 3/21/95 10/8/92 228 437 2/28/95 Hsia et al. V AV 5,393,708 6/10/92 569 427 Nguyen et al. L AW 5,356,722 10/18/94 8/17/92 579 Kwok et al. 427 12/21/93 5,271,972 ∠ AX 6/14/90 67 437 Pierce et al. 3/10/92 AY 5,094,972 2/1/90 427 255.3 Hochberg et al. 2/12/91 ΑZ 4,992,306 12/26/89 659.1 156 Stefano et al. 11/20/90 4,971,655 BA 5/12/88 437 228 · Haskell et al. 10/9/90 4,962,064 BB225 12/28/87 437 Doklan et al. BC 4,851,370 7/25/89 225-10/28/85 Chow et al. 437 12/6/88 4,789,648 BD 590 3/29/85 29 Hulseweh BE 4,614,021 9/30/86

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